

A2

2. (Amended) A semiconductor device according to claim 1 wherein said first conductive path has a smaller size than that of the rear surface of said semiconductor chip, said third conductive path has a larger size than that of said second conductive path.

A3

5. (Amended) A semiconductor device according to claim 2, wherein the insulating material is provided between said wiring extended to the rear surface of said semiconductor chip and said semiconductor chip or between said third conductive path and said semiconductor chip.

A4

8. (Amended) A semiconductor device according to claim 1, wherein the side of each of said conductive paths is curved to mate with said insulating resin.

A5

11. (Amended) A semiconductor device according to claim 10, further comprising a conductive film selectively covering said conductive paths and having made of material selected from the group consisting of nickel, silver and gold.

12. (Amended) A semiconductor device according to claim 1, wherein said first conductive path is coupled with a conductive pattern formed on a mounting board through a thermally conductive material.

A6

14. (Amended) A semiconductor device comprising:
a plurality of conductive paths electrically separated from one another by a trench;
a semiconductor chip connected with at least one of said conductive paths through a thermal conductive material; and
insulating resin which covers said semiconductor chip, is embedded in the trench among said plurality of conductive paths and integrally supports the conductive paths, rear surface of which are at least partially exposed from the insulating resin,
wherein at least another one of said conductive paths is disposed at a periphery of said semiconductor chip and extends underneath the chip and coupled to the chip through an insulating material to form an external terminal.--
